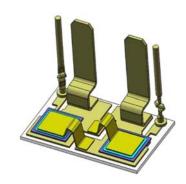


Rev.1.3 Oct.20 2023

# DBC040C/xxKQ-KGxA

#### **Description**

- 1) Components adopt vacuum welding to well control void and rated voltage up to 1600V.
- 2) A package of two inverse parallel SCRs.
- 3) Thyristor chips are welding on the ceramic copper clad laminate, products with high electricity ability, excellent heat dissipation ability.



#### **Typical Application**

Constant temperature system, CNC machine, remote control system, lighting control, power compensation and so on.

#### **Absolute Maximum Ratings** (Packaged into modules, unless otherwise specified, T<sub>CASE</sub>=25℃)

_ ,	Test Conditions	Symbol	Values		
Parameter			12	16	Unit
Operating junction temperature range		TJ	-40~+125		$^{\circ}\!\mathbb{C}$
Repetitive peak off-state voltage	TJ=25℃	$V_{DRM}$	1200	1600	V
Repetitive peak reverse voltage	TJ=25℃	$V_{RRM}$	1200	1600	V
Non-repetitive peak off-state voltage	TJ=25℃	V <sub>DSM</sub>	1300	1700	V
Non-repetitive peak reverse voltage	TJ=25℃	V <sub>RSM</sub>	1300	1700	V
Average on-state current	Tc=80℃	I <sub>T(AV)</sub>	4	.0	Α
RMS on-state current	Tc=80℃	I <sub>T(RMS)</sub>	6	0	Α
Non-repetitive surge peak on-state current	t <sub>P</sub> =10ms V <sub>R</sub> =0.6V <sub>RRM</sub>	Ітѕм	800		А
I <sup>2</sup> t value for fusing	t <sub>P</sub> =10ms V <sub>R</sub> =0.6V <sub>RRM</sub>	l <sup>2</sup> t	32	00	A <sup>2</sup> s
Critical rate of rise of on-state current	Ig =2×IgT	di/dt	1	50	A/µs

#### **Electrical Characteristics** (Packaged into modules, unless otherwise specified, T<sub>CASE</sub>=25°C)

Parameter	Test Conditions	Symbol	Values	Unit
Peak on-state voltage	I <sub>TM</sub> =120A,t <sub>P</sub> =380µs	Vтм	≤1.8	V
	V <sub>D</sub> =V <sub>DRM</sub>			
Repetitive peak off-state current	Tc=25℃	I <sub>DRM1</sub>	≤50	μΑ
	Tc=125℃	I <sub>DRM2</sub>	≤10	mA

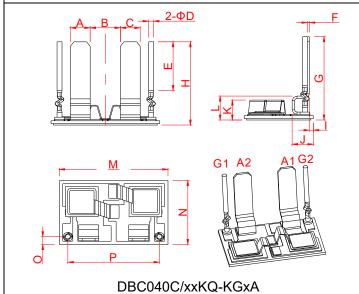


## **Solid DBC Modules**

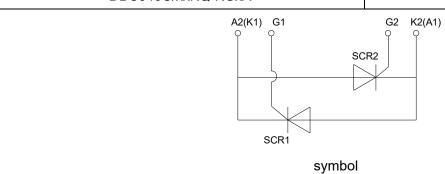
	V <sub>R</sub> =V <sub>RRM</sub>			
Repetitive peak reverse current	Tc=25℃	I <sub>RRM1</sub>	≤50	μA
	Tc=125℃	I <sub>RRM2</sub>	≤10	mA
Triggering gate current	V <sub>D</sub> =12V R <sub>L</sub> =30Ω	lgт	10-80	mA
Latching current	Ig=1.2 Igт	lι	≤250	mA
Holding current	Iτ=1A	Ін	≤150	mA
Triggering gate voltage	V <sub>D</sub> =12V R <sub>L</sub> =30Ω	V <sub>GT</sub>	≤1.3	V
Non triggering gate voltage	V <sub>D</sub> =V <sub>DRM</sub> T <sub>J</sub> =125℃	$V_{GD}$	≥0.2	V
Critical rate of rise of voltage	V <sub>D</sub> =2/3V <sub>DRM</sub> T <sub>J</sub> =125℃ Gate Open	dv/dt	≥1000	V/µs

## **Mechanical Characteristics**

Chip size	7.6mm×7.6mm
Module size	22mm×14mm
Terminal height	19.2mm
Solder composition and melting point of DBC	Solder composition: Pb92.5%Sn5%Ag2.5%; melting point>295℃.



			Dima			
	Dimensio			ISIONS		
Ref	Millimeters			Inches		
	Min	Тур	Max	Min	Тур	Max
Α	3.7	4	4.3	0.146	0.157	0.169
В	5.6	6.1	6.6	0.220	0.24	0.26
С	3.7	4	4.3	0.146	0.157	0.169
D		1			0.039	
Е		10.65			0.419	
F	0.3	0.5	0.7	0.012	0.020	0.028
G			19.2			0.756
Н			19.2			0.756
I	0.3	8.0	1.3	0.012	0.031	0.051
J	3.8	4.3	4.8	0.150	0.169	0.189
K			6			0.236
L			6.2			0.244
М	21.7	22	22.3	0.854	0.866	0.878
N	13.7	14	14.3	0.539	0.551	0.563
0	1.2	1.7	2.2	0.047	0.067	0.087
Р	18	18.5	19	0.709	0.728	0.748

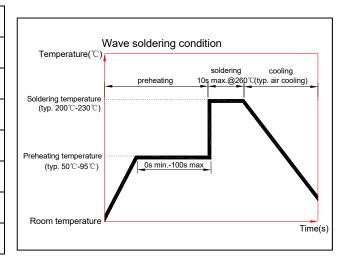






**Soldering Process Requirements** 

a. Hand soldering iron welding			
Soldering temperature	≤260℃		
Soldering time	≤10s		
b. Wave soldering (see figure at right)			
Preheating temperature	≤125℃		
Preheating time	≤100s		
Soldering temperature	≤260℃		
Soldering time	≤10s		



#### **Working Conditions**

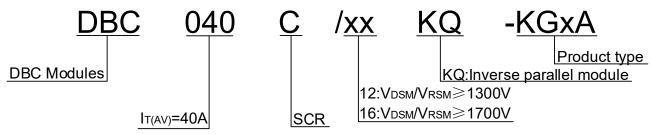
1) No severe mechanical shock as impact and drop off in the process of transportation, storage and working of product.

2) Storage conditions

Temperature: 5~40°C Relative humidity: ≤45%

Storage time: 3 days for the open package; 3 months for the closed package

### **Ordering Information**



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